ABSTRACT

A host information memory is provided in a semiconductor memory card and a data write start address and a data size supplied by an access unit are stored. A free physical area generation section determines whether or not to perform erasing of an invalid block of a nonvolatile memory when writing of data based on the data write start address and data size, and determines the number of blocks to be erased. When erasing, writing of data and erasing of invalid blocks are simultaneously performed with respect to different memory chips. Erase process of data, herewith, can be optimized and high speed access from the access unit to a semiconductor memory card can be realized.